

ABSTRACT OF THE DISCLOSURE

A surface emitting semiconductor laser includes a substrate, a first mirror that is formed on the substrate and includes semiconductor layers of a first conduction type, a  
5 second mirror that includes semiconductor layers of a second conduction type, an active region disposed between the first and second mirrors, a current confinement layer that is disposed between the first and second mirrors and includes a selectively oxidized region, and an inorganic insulation film.  
10 A mesa structure includes at least the second mirror and the current confinement layer. The inorganic insulation film covers at least a side surface of the mesa structure and having an internal stress equal to or less than  $1.5 \times 10^9$  dyne/cm<sup>2</sup>.

15